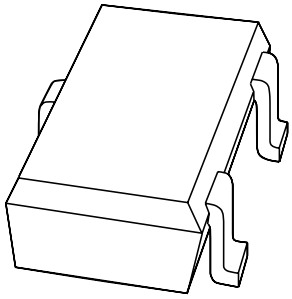
DATA SHEET



BC849W; BC850W
NPN general purpose transistors

Product specification
1997 Jun 20
Supersedes data of November 1992
File under Discrete Semiconductors, SC04

Philips
Semiconductors

PHILIPS

NPN general purpose transistors BC849W; BC850W

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

APPLICATIONS

- Low noise stages in tape recorders, hi-fi amplifiers and other audio-frequency equipment.

DESCRIPTION

NPN transistor in a SOT323 plastic package.
PNP complements: BC859W and BC860W.

MARKING

TYPE NUMBER	MARKING CODE	TYPE NUMBER	MARKING CODE
BC849W	2Dt	BC850W	2Ht
BC849BW	2Bt	BC850BW	2Ft
BC849CW	2Ct	BC850CW	2Gt

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

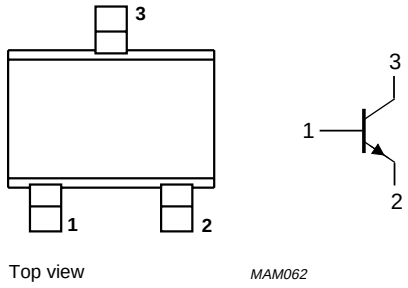


Fig.1 Simplified outline (SOT323) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BC849W		–	30	V
	BC850W		–	50	V
V_{CEO}	collector-emitter voltage	open base			
	BC849W		–	30	V
	BC850W		–	45	V
I_{CM}	peak collector current		–	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	–	200	mW
h_{FE}	DC current gain	I_C = 2 mA; V_{CE} = 5 V	200	800	
f_T	transition frequency	I_C = 10 mA; V_{CE} = 5 V; f = 100 MHz	100	–	MHz

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BC849W		–	30	V
	BC850W		–	50	V
V_{CEO}	collector-emitter voltage	open base			
	BC849W		–	30	V
	BC850W		–	45	V
V_{EBO}	emitter-base voltage	open collector	–	5	V
I_C	collector current (DC)		–	100	mA
I_{CM}	peak collector current		–	200	mA
I_{BM}	peak base current		–	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	200	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

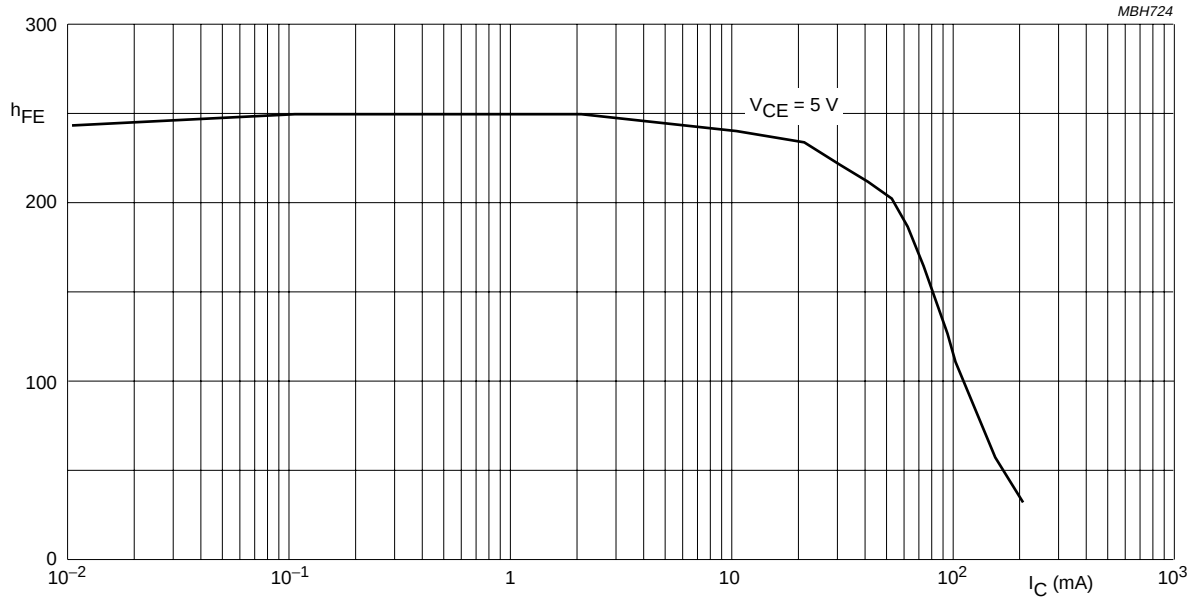
CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	I_E = 0; V_{CB} = 30 V	–	–	15	nA
		I_E = 0; V_{CB} = 30 V; T_j = 150 °C	–	–	5	μA
I_{EBO}	emitter cut-off current	I_C = 0; V_{EB} = 5 V	–	–	100	nA
h_{FE}	DC current gain	I_C = 2 mA; V_{CE} = 5 V; see Figs 2 and 3				
	BC849W; BC850W		200	–	800	
	BC849BW; BC850BW		200	–	450	
	BC849CW; BC850CW		420	–	800	
V_{CEsat}	collector-emitter saturation voltage	I_C = 10 mA; I_B = 0.5 mA	–	–	250	mV
		I_C = 100 mA; I_B = 5 mA; note 1	–	–	600	mV
V_{BE}	base-emitter voltage	I_C = 2 mA; V_{CE} = 5 V	580	–	700	mV
		I_C = 10 mA; V_{CE} = 5 V	–	–	770	mV
C_c	collector capacitance	I_E = i_e = 0; V_{CB} = 10 V; f = 1 MHz	–	–	3	pF
C_e	emitter capacitance	I_C = i_c = 0; V_{EB} = 500 mV; f = 1 MHz	–	11	–	pF
f_T	transition frequency	I_C = 10 mA; V_{CE} = 5 V; f = 100 MHz	100	–	–	MHz
F	noise figure	I_C = 200 μA; V_{CE} = 5 V; R_S = 2 kΩ; f = 10 Hz to 15.7 kHz	–	–	4	dB
		I_C = 200 μA; V_{CE} = 5 V; R_S = 2 kΩ; f = 1 kHz; B = 200 Hz	–	–	4	dB

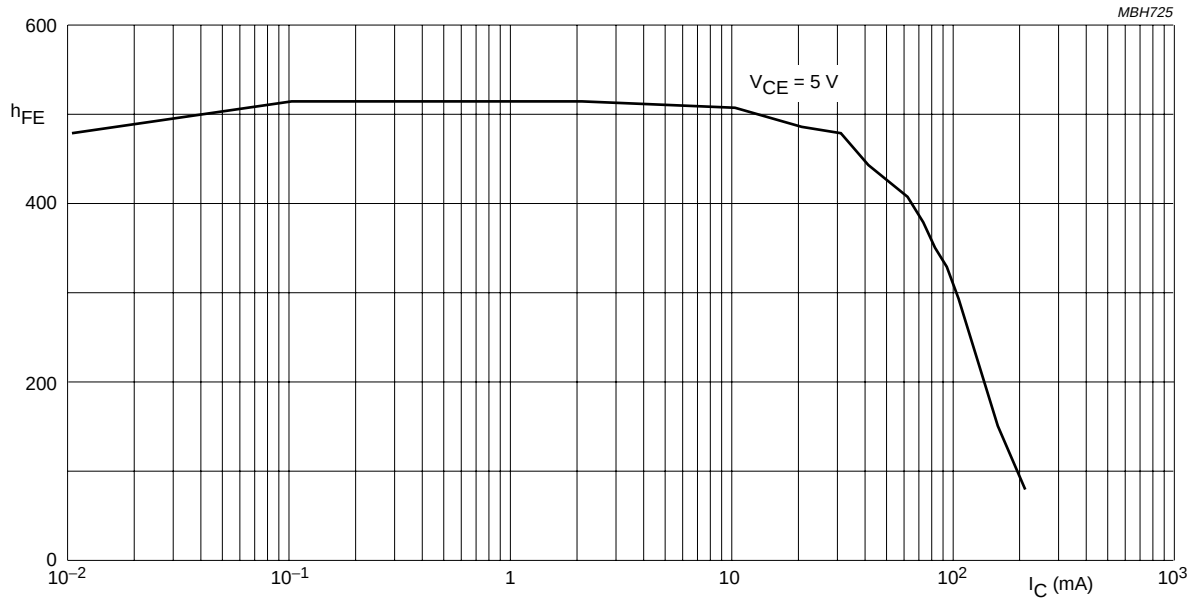
Note

1. Pulse test: $t_p \leq 300$ μs; $\delta \leq 0.02$.



BC849BW; BC850BW.

Fig.2 DC current gain; typical values.

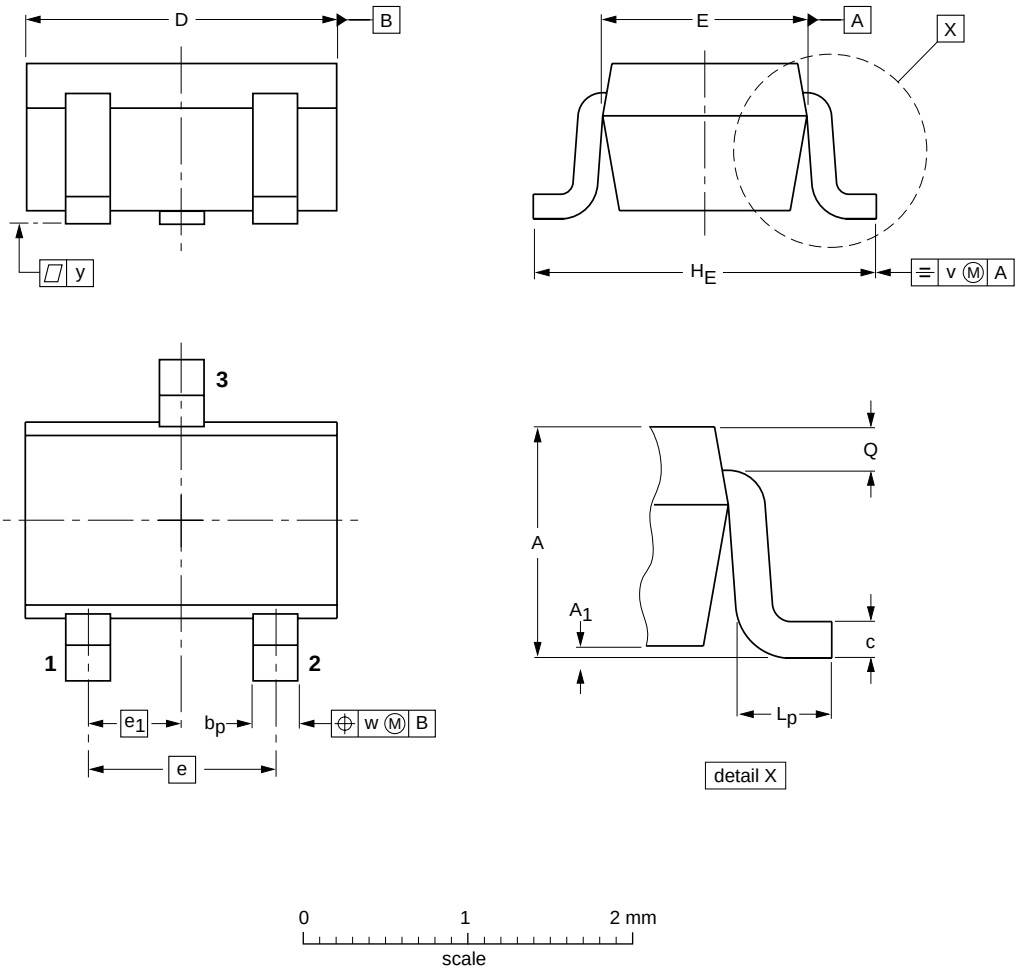


BC849CW; BC850CW.

Fig.3 DC current gain; typical values.

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT323**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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